

1.5V Drive Nch MOSFET

RQ1C075UN

Structure

Silicon N-channel MOSFET

Features

- 1) Low on-resistance.
- 2) High power package(TSMT8).
- 3) Low voltage drive(1.5V drive).

Application

Switching

Packaging specifications

| | • . | | |
|----------|------------------------------|--------|--|
| Type | Package | Taping | |
| | Code | TR | |
| | Basic ordering unit (pieces) | 3000 | |
| RQ1C075L | 0 | | |

● Absolute maximum ratings (Ta = 25°C)

| Parameter | | Symbol | ymbol Limits | |
|--------------------------------|------------|--------------------|--------------|----|
| Drain-source voltage | | V_{DSS} | 20 | V |
| Gate-source voltage | | V_{GSS} | ±10 | V |
| Drain current | Continuous | I_D | ±7.5 | Α |
| | Pulsed | I _{DP} *1 | ±30 | Α |
| Source current (Body Diode) | Continuous | I _S | 1 | Α |
| | Pulsed | I _{SP} *1 | 30 | Α |
| Power dissipation | | P _D *2 | 1.5 | W |
| Channel temperature | | Tch 150 | | °C |
| Range of storage temperature | | Tstg | -55 to +150 | °C |

^{*1} Pw≤10µs, Duty cycle≤1%

• Thermal resistance

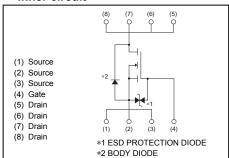
| Parameter | Symbol | Limits | Unit |
|--------------------|-------------|--------|------|
| Channel to Ambient | Rth (ch-a)* | 83.3 | °C/W |

^{*} Each terminal mounted on a ceramic board.

© Dimensions (Unit : mm) TSMT8 3.0 (8) (7) (6) (5) (1) (2) (3) (4) 0.65 0.32

Abbreviated symbol : XH

• Inner circuit



^{*2} Each terminal mounted on a ceramic board.

● Electrical characteristics (Ta = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---------------------------------|-----------------------|------|------|------|--------|---|
| Gate-source leakage | I_{GSS} | - | - | ±10 | μA | V _{GS} =±10V, V _{DS} =0V |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 20 | - | - | ٧ | I _D =1mA, V _{GS} =0V |
| Zero gate voltage drain current | I _{DSS} | 1 | - | 1 | μA | V _{DS} =20V, V _{GS} =0V |
| Gate threshold voltage | V _{GS (th)} | 0.3 | - | 1.0 | ٧ | V _{DS=} 10V, I _D =1mA |
| | | - | 11 | 16 | | I _D =7.5A, V _{GS} =4.5V |
| Static drain-source on-state | R * | ı | 14 | 20 | mΩ | I _D =7.5A, V _{GS} =2.5V |
| resistance | R _{DS (on)} | - | 17 | 24 | 1115.2 | I _D =3.7A, V _{GS} =1.8V |
| | | 1 | 20 | 40 | | I _D =1.5A, V _{GS} =1.5V |
| Forward transfer admittance | I Y _{fs} I* | 7 | - | - | S | I _D =7.5A, V _{DS} =10V |
| Input capacitance | C _{iss} | 1 | 1400 | ı | pF | V _{DS} =10V |
| Output capacitance | C _{oss} | 1 | 310 | - | pF | V _{GS} =0V |
| Reverse transfer capacitance | C _{rss} | 1 | 210 | - | pF | f=1MHz |
| Turn-on delay time | t _{d(on)} * | 1 | 15 | - | ns | I _D =3.7A, V _{DD} ≒10V |
| Rise time | t _r * | 1 | 50 | - | ns | V _{GS} =4.5V |
| Turn-off delay time | t _{d(off)} * | - | 100 | - | ns | R_L =2.7 Ω |
| Fall time | t _f * | - | 85 | - | ns | R_G =10 Ω |
| Total gate charge | Q _g * | - | 18 | _ | nC | I _D =7.5A, R _L =1.3Ω |
| Gate-source charge | Q _{gs} * | - | 3.2 | - | nC | V _{DD} ≒10V, R _G =10Ω |
| Gate-drain charge | Q _{gd} * | - | 2.9 | - | nC | V _{GS} =4.5V |

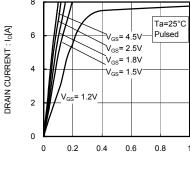
^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|-----------------|-------------------|------|------|------|------|---|
| Forward Voltage | V _{SD} * | - | - | 1.2 | V | I _s =7.5A, V _{GS} =0V |

^{*}Pulsed

• Electrical characteristic curves



DRAIN-SOURCE VOLTAGE : V_{DS}[V]
Fig.1 Typical Output Characteristics(I)

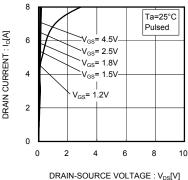
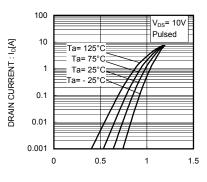


Fig.2 Typical Output Characteristics(II)



GATE-SOURCE VOLTAGE : V_{GS}[V] Fig.3 Typical Transfer Characteristics

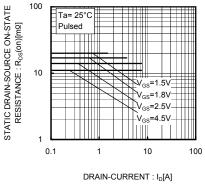


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

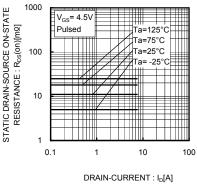


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

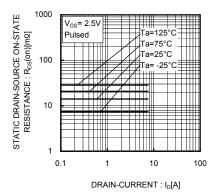


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(皿)

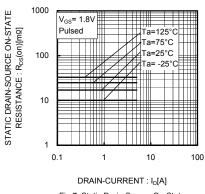


Fig.7 Static Drain-Source On-State
Resistance vs. Drain Current(IV)

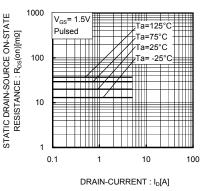


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

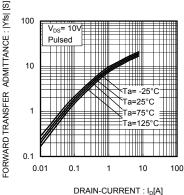


Fig.9 Forward Transfer Admittance
vs. Drain Current

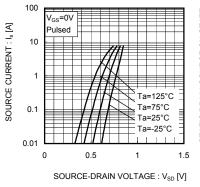
GATE-SOURCE VOLTAGE: V_{GS} [V]

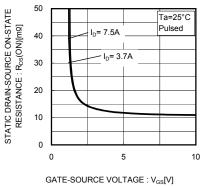
3

2

0

0





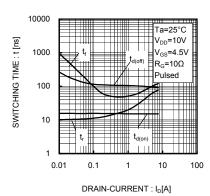


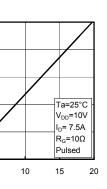
Fig.10 Reverse Drain Current

Fig.11 Static Drain-Source On-State

Resistance vs. Gate Source Voltage

Fig.12 Switching Characteristics

vs. Sourse-Drain Voltage



10000 Ta=25°C f=1MHz CAPACITANCE: C [pF] √_{GS}=0V 1000 C_{rss} 100 0.01 0.1 10 100 DRAIN-SOURCE VOLTAGE : $V_{DS}[V]$

TOTAL GATE CHARGE : Qg [nC]

Fig.13 Dynamic Input Characteristics

Fig.14 Typical Capacitance vs. Drain-Source Voltage

Measurement circuits

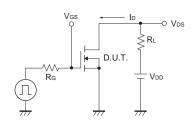


Fig.1-1 Switching time measurement circuit

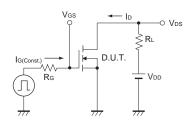


Fig.2-1 Gate charge measurement circuit

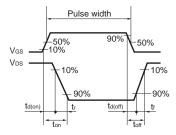


Fig.1-2 Switching waveforms

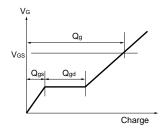


Fig.2-2 Gate Charge Waveform

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